SEMICONDUCTOR DEVICE

ABSTRACT

A semiconductor device 1 is equipped with a first substrate 3 on which a first semiconductor chip 2 is mounted, a second substrate 5 on which a second semiconductor chip 4 is mounted, and connecting sections 6 that electrically connect the first substrate 3 and the second substrate 5. The first substrate 3 has build-up layers 31A and 31B in each of which an insulating layer 311 containing a resin and conductor interconnect layers 312 and 313 are laminated alternately, and the respective conductor interconnect layers 312 are connected by a conductive layer 314 provided in via holes of the insulating layers 311. The second substrate 5 also has build-up layers 31A and 31B. In the insulating layers 311 of the build-up layers in at least one substrate of the first substrate 3 and the second substrate 5, the average coefficient of thermal expansion of at least one insulating layer along the substrate inplane direction at from 25 degrees centigrade to the glass transition point is 35 ppm/degrees centigrade or less, and the average coefficient of thermal expansion along the substrate thickness direction is 35 ppm/degrees centigrade or less.

Figure 2